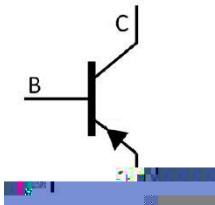


SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

High f_T , high V_{CEO} , , 2SC2881G



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-800	mA
Collector Base-Continuous	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation*	$*P_C$	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*mounted on ceramic substrate($250\text{mm}^2 \times 0.8\text{t}$)

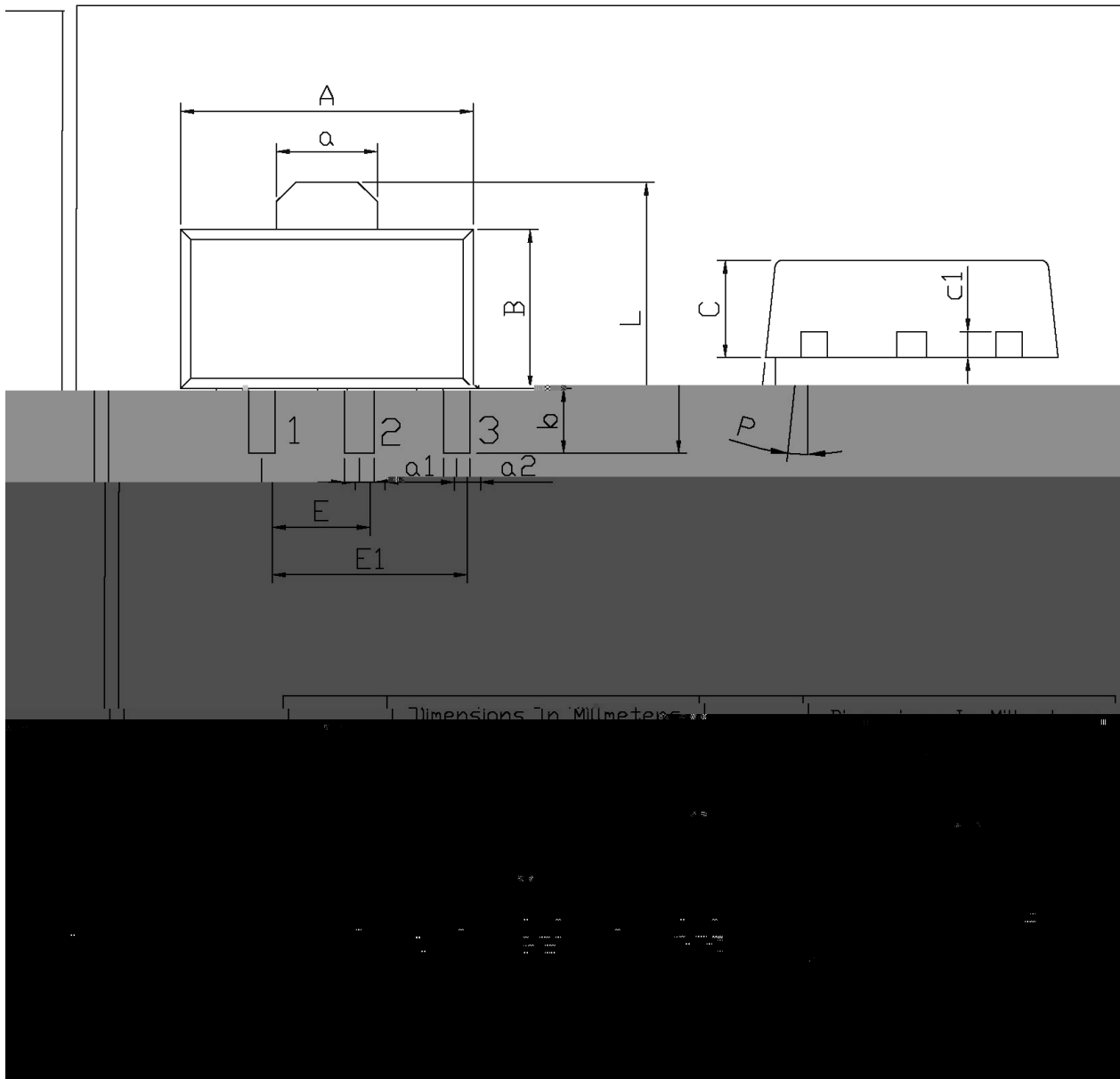
* $250\text{mm}^2 \times 0.8\text{t}$

Parameter	Symbol	Test Conditions	
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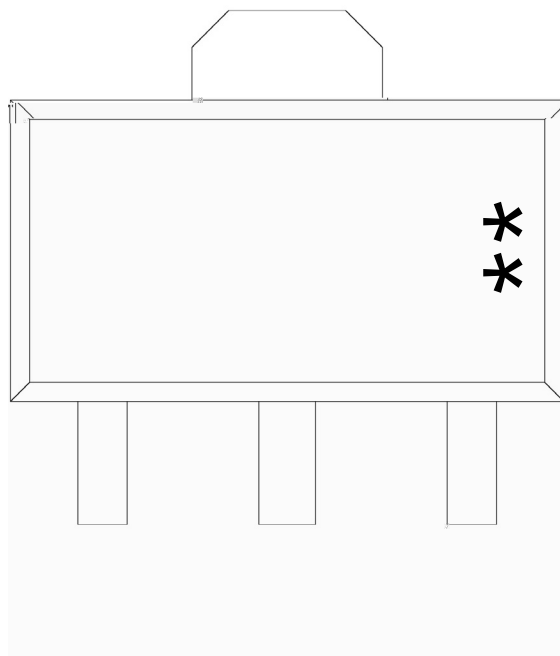
⊂ É Ò Ì f / Package Dimensions

2SA1201G

单位: mm



1. 1.1 / Marking Instructions



G

D

O h_{FE}

**

Note:

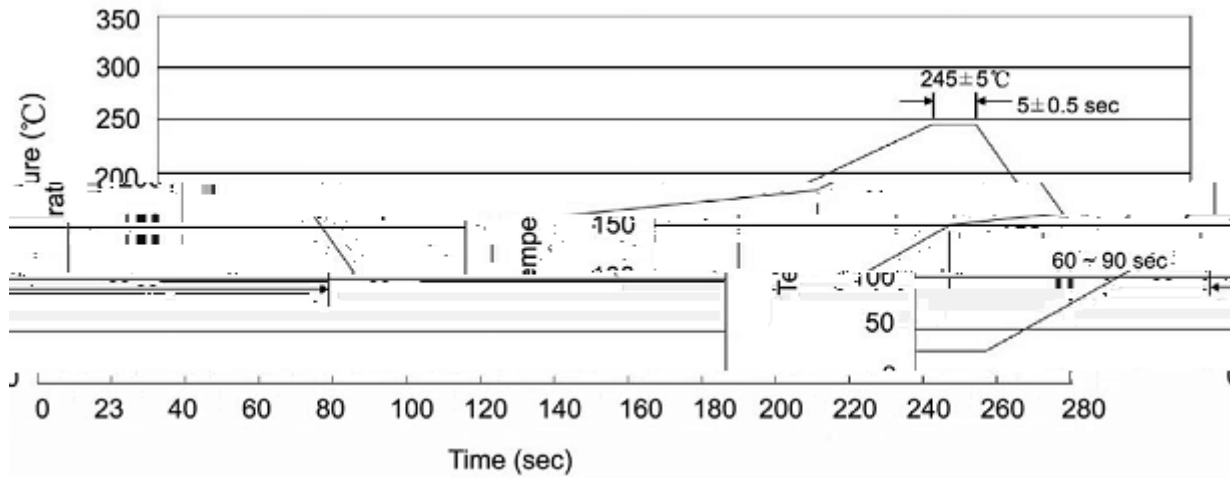
G: Halogen Free Product.

D: Product Type.

O: h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0l uhh,



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		

Notices